

Appl. No. 10/605,808  
Amdt. dated January 02, 2006  
Reply to Office action of October 03, 2005

**Amendments to the Specification:**

Please replace paragraph [0018] with the following amended paragraph:

[0018] In the three aforementioned embodiments, another transparent conductive layer may be formed between the second wiring electrode and the second contact layer. The shape of the aforementioned micro-reflection structure comprises at least one shape of the following: a hemisphere or a pyramid. The aforementioned micro-reflection structure carrier comprises at least one material selected from the group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, AlGaAs, Si, SiC, glass, BN, AlN, and Ge. The aforementioned micro-reflection structure conductive carrier comprises at least one material selected from the group consisting of Si, GaAs, SiC, GaP, GaAsP, InGaP, AlGaInP, AlGaAs, BN, and AlN. The aforementioned transparent carrier comprises at least one material selected from the group consisting of GaP, SiC, Al<sub>2</sub>O<sub>3</sub>, and glass. The aforementioned reflection layer comprises at least one material selected from the group consisting of Sn, Al, Au, Pt, Zn, Ag, Ti, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn. The aforementioned transparent conductive layer comprises at least one material selected from the group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, and zinc tin oxide. The aforementioned first and second cladding layer comprise at least one material selected from the group consisting of AlGaInP, AlN, GaN, AlGaIn, InGaIn, and AlInGaIn. The aforementioned light emitting layer comprises at least one material selected from the group consisting of AlGaInP, GaN, InGaIn, and AlInGaIn. The aforementioned first and second contact layer comprise at least one material selected from the group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, AlGaAs, GaN, InGaIn, and AlGaIn. The aforementioned transparent adhesive layer comprises at least one material selected from the group consisting of polyimide (PI), benzocyclobutane, benzocyclobutene (BCB), and perfluorocyclobutane (PFCB). The aforementioned first and second reaction layer comprise at least one material selected from the group consisting of SiNx, Ti, and Cr.